

AMENDMENTS TO THE SPECIFICATION:

Please replace paragraph [0061] with the following amended paragraph:

B¹ Fig. 13 is a characteristic diagram showing a relationship between $(C_{\text{MIN}} + C_{\text{MIS}})/C_{\text{MIS}}$ of the semiconductor ~~involatile~~ nonvolatile storage element according to the first embodiment of the invention shown in Fig. 2I and a distance 114(h) between a bottom face of a first conductor layer and upper faces of a third and a fourth conductor;
